

4. The integrated circuit of claim 1, wherein the diffusion region comprises two individual diffusion regions disposed respectively on each side of the conductive line.

B1 5. (Amended) An integrated circuit comprising a conductive line received, the conductive line not being a gate electrode, over a semiconductive substrate and a diffusion region within the substrate proximate the line, a conductive material being received over the line and interconnecting it with the diffusion region, the diffusion region being effectively reverse biased to preclude shorting between the conductive line and the substrate through the conductive material for selected magnitudes of current provided through the conductive line.

6. The integrated circuit of claim 5, wherein the conductive material comprises metal.

7. The integrated circuit of claim 5, wherein a portion of the diffusion region is disposed under conductive portions of the conductive line.

8. The integrated circuit of claim 5, wherein the diffusion region comprises two individual diffusion regions disposed respectively on each side of the conductive line.

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Please add Claim 50.

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B2 50. (New) The integrated circuit of claim 1, wherein the conductive line is in electrical communication with the diffusion region.

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